

Silicon NPN Power Transistors

2SD350A

DESCRIPTION

www.datasheet4u.com

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING(see fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |

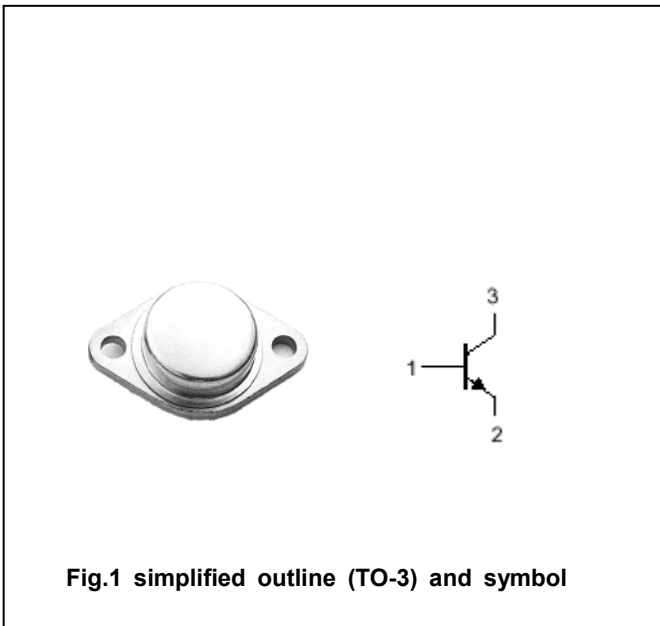


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|---------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 700 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 5 | A |
| I _{CM} | Collector current-peak | | 7 | A |
| P _T | Total power dissipation | T _C =90□ | 22 | W |
| T _j | Junction temperature | | 150 | □ |
| T _{stg} | Storage temperature | | -55~150 | □ |

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------|--------------------------------------|------------------------------------|-----|------|-----|---------------|
| $V_{CEO(SUS)}$ | Collector-emitter sustaining voltage | $I_C=0.1\text{A}; I_B=0$ | 700 | | | V |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage | $I_E=10\text{mA}; I_C=0$ | 5 | | | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C=4.5\text{A}; I_B=2\text{A}$ | | | 1.0 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C=4.5\text{A}; I_B=2\text{A}$ | | | 1.3 | V |
| I_{CBO} | Collector cut-off current | $V_{CB}=800\text{V}; I_E=0$ | | | 10 | μA |
| h_{FE-1} | DC current gain | $I_C=1\text{A}; V_{CE}=5\text{V}$ | 8 | | | |
| h_{FE-2} | DC current gain | $I_C=4\text{A}; V_{CE}=10\text{V}$ | 3 | | | |

PACKAGE OUTLINE

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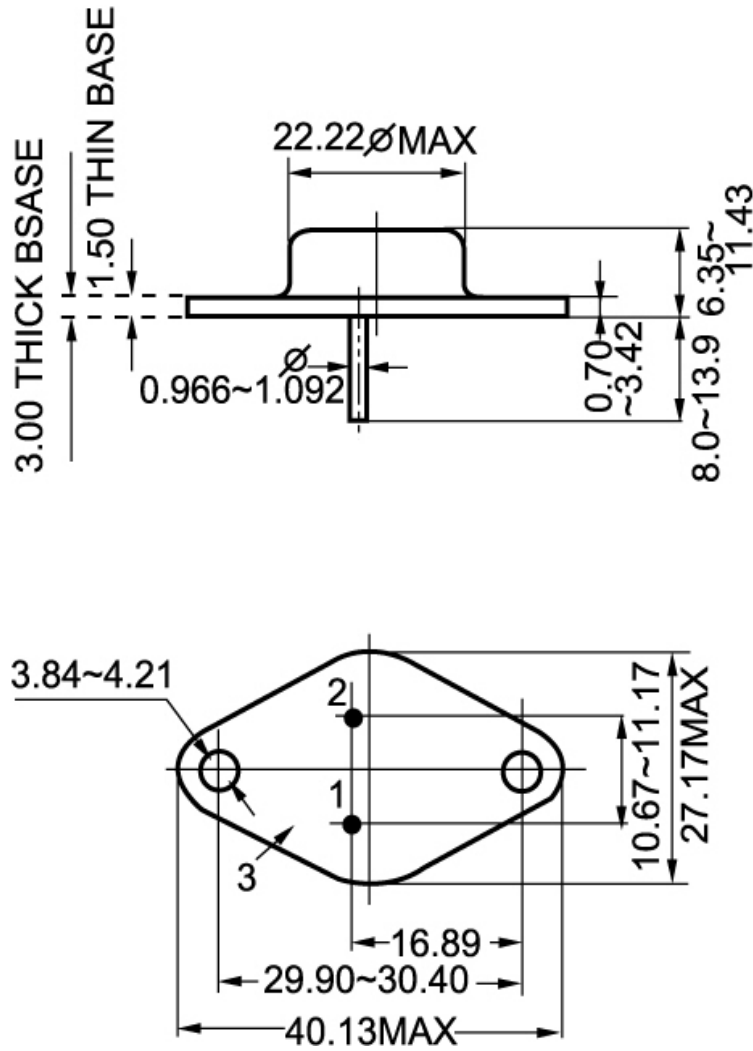


Fig.2 Outline dimensions